

# MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

## Amplifier Transistors

### NPN Silicon

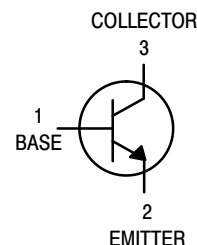


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#### Features

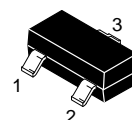
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



#### MAXIMUM RATINGS

Rating	Symbol	6428LT1	6429LT1	Unit
Collector–Emitter Voltage	$V_{CEO}$	50	45	Vdc
Collector–Base Voltage	$V_{CBO}$	60	55	Vdc
Emitter–Base Voltage	$V_{EBO}$	6.0		Vdc
Collector Current – Continuous	$I_C$	200		mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



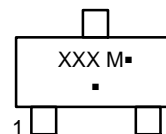
SOT-23 (TO-236)  
CASE 318  
STYLE 6

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

#### MARKING DIAGRAM



XXX = Specific Device Code  
MMBT6428LT1 – 1KM  
NSV/MMBT6429LT1 – M1L  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT6428LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSVMMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub> MMBT6428 MMBT6429 / NSVMMBT6429	50 45	– –	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , I <sub>E</sub> = 0) (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub> MMBT6428 MMBT6429 / NSVMMBT6429	60 55	– –	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> )	I <sub>CES</sub>	–	0.1	μA <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 30 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	0.01	μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	0.01	μA <sub>dc</sub>

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 0.01 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )  (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )  (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )  (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub> MMBT6428 MMBT6429 / NSVMMBT6429  MMBT6428 MMBT6429 / NSVMMBT6429  MMBT6428 MMBT6429 / NSVMMBT6429  MMBT6428 MMBT6429 / NSVMMBT6429	250 500  250 500  250 500  250 500	– –  650 1250  – –  – –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0.5 mA <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.2 0.6	V <sub>dc</sub>
Base–Emitter On Voltage (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	V <sub>BE(on)</sub>	0.56	0.66	V <sub>dc</sub>

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	100	700	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	3.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

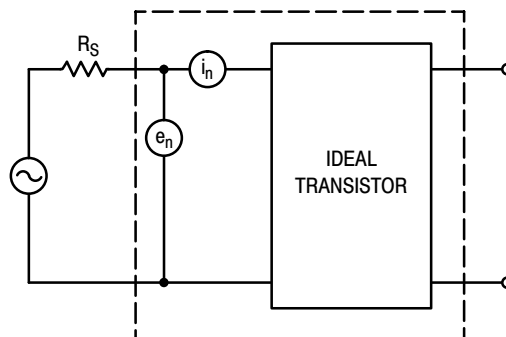


Figure 1. Transistor Noise Model

# MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

## NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

### NOISE VOLTAGE

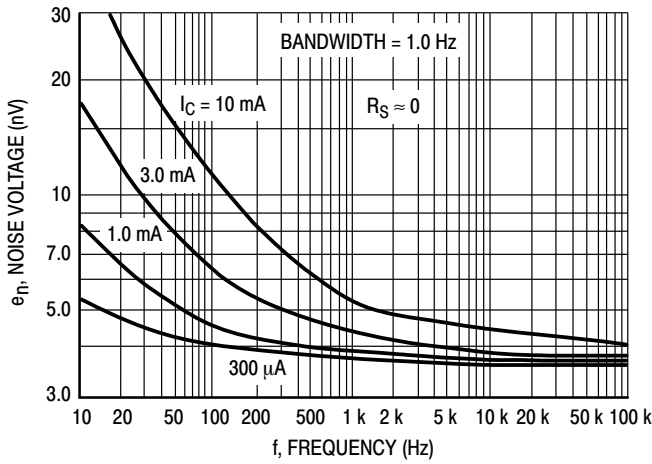


Figure 2. Effects of Frequency

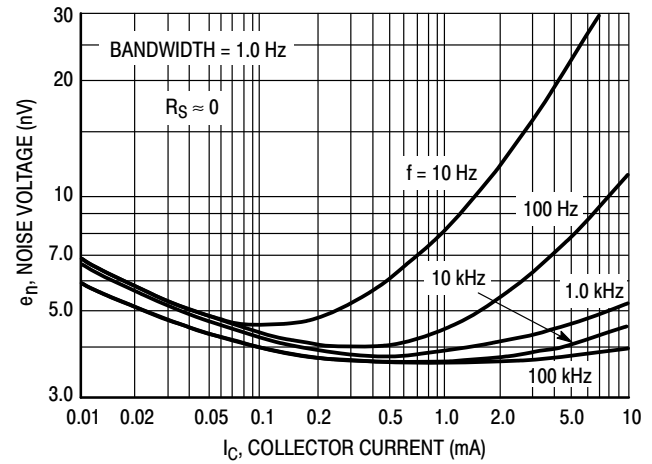


Figure 3. Effects of Collector Current

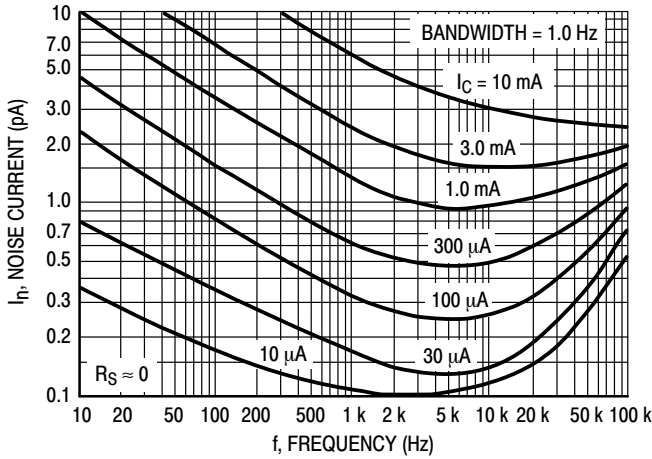


Figure 4. Noise Current

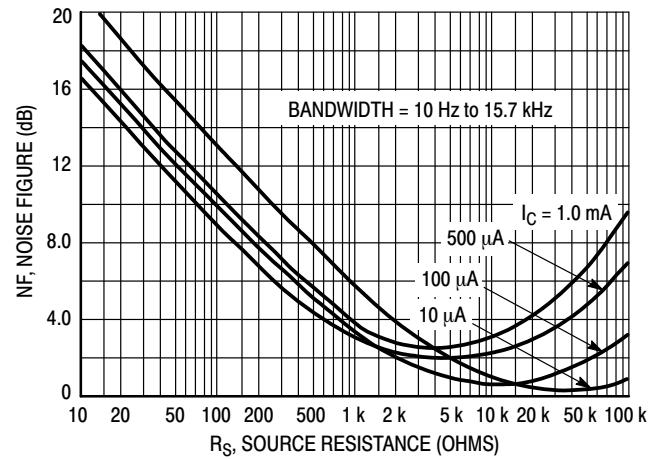


Figure 5. Wideband Noise Figure

### 100 Hz NOISE DATA

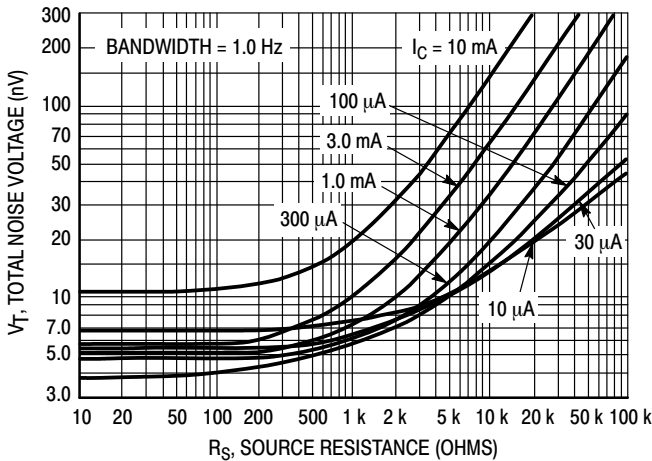


Figure 6. Total Noise Voltage

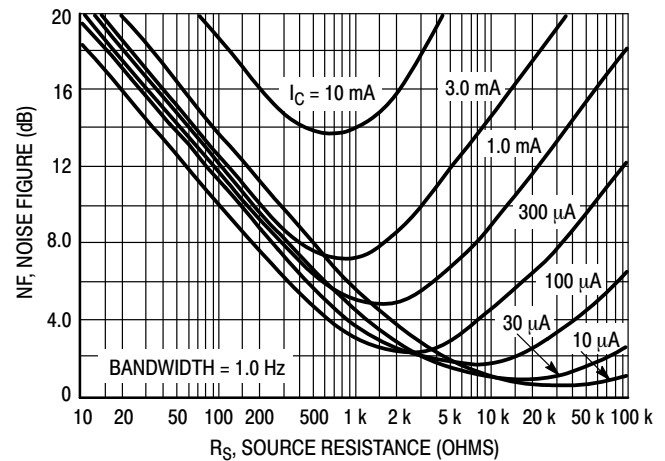


Figure 7. Noise Figure

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

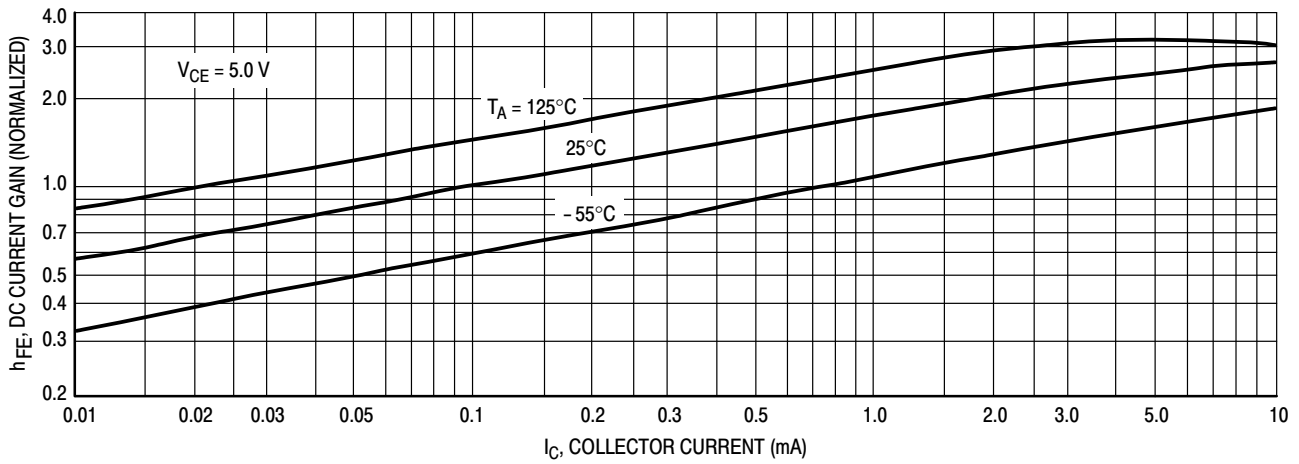


Figure 8. DC Current Gain

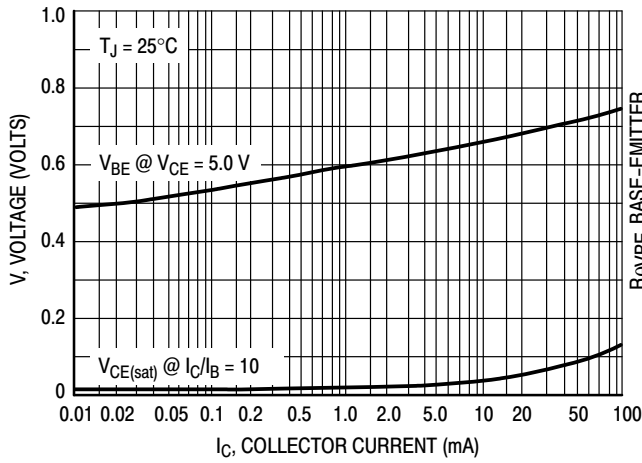


Figure 9. "On" Voltages

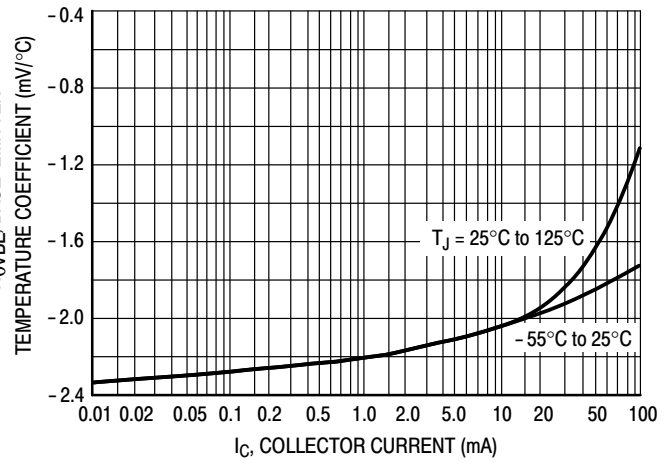


Figure 10. Temperature Coefficients

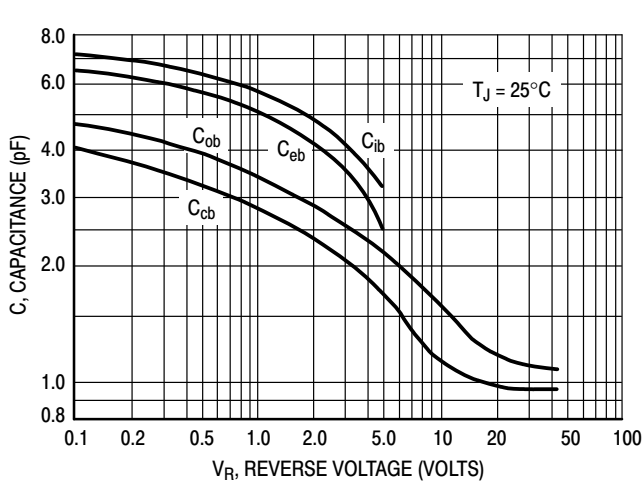


Figure 11. Capacitance

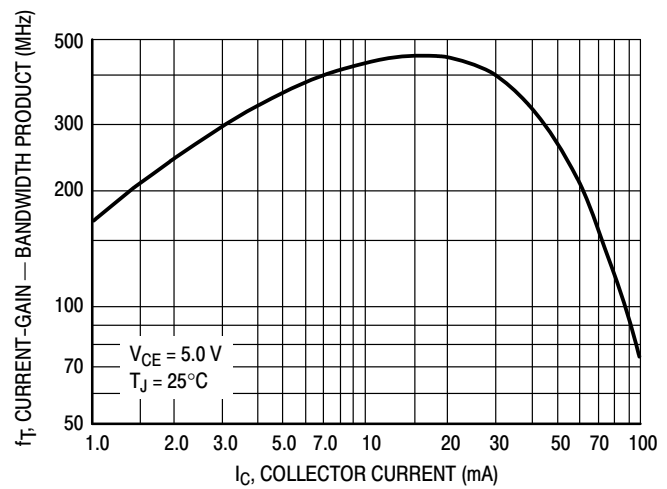


Figure 12. Current-Gain — Bandwidth Product

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**



**SOT-23 (TO-236)**  
**CASE 318**  
**ISSUE AT**

DATE 01 MAR 2023

- |   |   |   |   |   |   |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:<br>CANCELLED                            | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE  |   |   |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE      | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE     | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE      | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE | STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE          |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN       | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT   | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE           | STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION |
| STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE     |   |   |   |   |

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